



# American Microsemiconductor, Inc.

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## Features

- Low Leakage Current
- Flat Junction Capacitance
- High Mechanical Strength
- Options for screening in accordance with MIL-S-19500/200B for JAN AND JANTX are available by adding HJ or HXJ prefixes respectively to part numbers.  
 For example, designate HJ1N270 for a JAN screen.

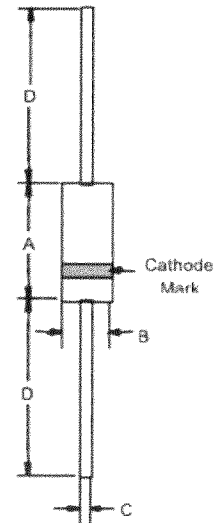
## Electrical Characteristics @ 25°C Unless Otherwise Specified

Peak Inverse Voltage	PIV	100V	
Average Rectified Current	$I_O$	60mA	
Peak Operating Current	$I_{OS}$	325mA	
Peak Forward Surge Current	$I_{FSM}$	500mA	8.3ms, half sine
Maximum Instantaneous Forward Voltage	$V_F$	1.00V	$I_{FM} = 150mA;$ $T_J = 25^\circ C^*$
Maximum Reverse Current	$I_R$	100 $\mu A$	$V_R = 50Volts$ $T_J = 25^\circ C$
Typical Junction Capacitance	$C_J$	0.8pF	Measured at 1.0MHz, $V_R=1.0V$

\*Pulse test: Pulse width 300  $\mu sec$ , Duty cycle 2%

## 1N270 Germanium Diode 100 Volt

DO-7



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	---	300	---	7.62	
B	---	107	---	2.72	∅
C	.018	.022	0.46	0.56	∅
D	1.000	---	25.40	---	